TOSHIBA Photocoupler GaAlAs Ired & Photo-IC

TLP2601

Isolated Line Receiver
Simplex / Multiplex Data Transmission
Computer-Peripheral Interface
Microprocessor System Interface
Digital Isolation For A/D, D/A Conversion
Direct Replacement For HCPL-2601

The TOSHIBA TLP2601 a photocoupler which combines a GaA ℓ As IRed as the emitter and an integrated high gain, high speed photodetector. The output of the detector circuit is an open collector, Schottky clamped transistor.

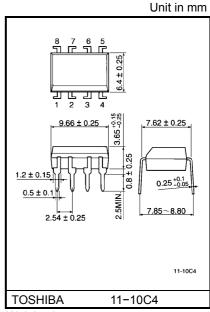
A Faraday shield integrated on the photodetector chip reduces the effects of capacitive coupling between the input LED emitter and the high gain stages of the detector. This provides an effective common mode transient immunity of $1000V/\mu s$.

- Input current thresholds: IF = 5mA max.
- Isolation voltage: 2500Vrms min.
- Switching speed: 10MBd
- Common mode transient immunity: 1000V/µs min.
- Guaranteed performance over temp.: 0°C~70°C
- UL Recognized: UL1577, file No. E67349

Truth Table (positive logic)

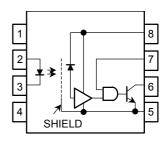
Input	Enable	Output
Н	Н	L
L	Н	Н
Н	L	Н
L	L	Н

A 0.01 to $0.1\mu F$ bypass capacitor must be connected between pins 8 and 5 (see Note 1).

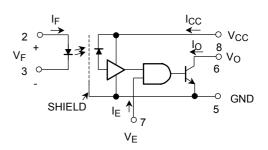


Weight: 0.54g

Pin Configuration (top view)



Schematic



Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current, low level	I _{FL}	0	_	250	μΑ
Input current, high level	I _{FH}	6.3 (*)		20	mA
Supply voltage, output	V _{CC}	4.5	_	5.5	V
High level enable voltage	V _{EH}	2.0	_	V _C C	V
Low level enable voltage	V _{EL}	0	_	0.8	V
Fan out (TTL load)	N	_	_	8	_
Operating temperature	T _{opr}	0		70	°C

^{(*) 6.3}mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0mA or less.

Maximum Ratings (no derating required)

	Characteristic		Rating	Unit	
ED.	Forward current	I _F	20	mA	
쁘	Reverse voltage	V _R	5	V	
	Output current	IO	25	mA	
	Output voltage	Vo	-0.5~7	V	
or.	Supply voltage	V _{CC}	7	V	
Detector	(1 minute maximum)	∨ CC	7	V	
ă	Enable input voltage	VF	5.5	V	
	(not to exceed V _{CC} by more than 500mV)	> E	5.5	V	
	Output collector power dissipation	Po	40	mW	
Oper	Operating temperature range		-40~85	°C	
Storage temperature range		T _{stg}	-55~125	°C	
Lead	solder temperature (10s) (**)	T _{sol}	260	°C	
Isolat	tion voltage	D\/-	2500	Vrms	
(R.H.	≤ 60%,AC 1min., (Note 10)	BV _S	3540	V _{dc}	

^{(**) 1.6}mm below seating plane.

Electrical Characteristics (Ta = 0° C \sim 70°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
High level output current	Гон	$V_{CC} = 5.5V, V_O = 5.5V$ $I_F = 250\mu A, V_E = 2.0V$	_	1	250	μА
Low level output voltage	V _{OL}	$V_{CC} = 5.5V, I_F = 5mA$ $V_E = 2.0V, I_{OL}(sinking) = 13mA$	_	0.4	0.6	V
High level supply current	Іссн	V _{CC} = 5.5V, I _F = 0, V _E = 0.5V	_	7	15	mA
Low level supply current	ICCL	$V_{CC} = 5.5V, I_F = 10mA$ $V_E = 0.5V$	_	12	19	mA
Low level enable current	I _{EL}	V _{CC} = 5.5V, V _E = 0.5V	_	-1.6	-2.0	mA
High level enable current	lEH	V _{CC} = 5.5V, V _E = 2.0V	_	-1	_	mA
High level enable voltage	V _{EH}	(Note 11)	2.0	_	_	V
Low level enable voltage	V _{EL}	_	_	_	0.8	
Input forward voltage	V _F	I _F = 10mA, Ta = 25°C	_	1.65	1.75	V
Input reverse breakdown voltage	BV _R	I _R = 10μA, Ta = 25°C	5	_	_	V
Input capacitance	C _{IN}	V _F = 0, f = 1MHz	_	45	_	pF
Input diode temperature coefficient	$\Delta V_F/\Delta T_A$	I _F = 10mA	_	-2.0	_	mV / °C
Input-output insulation leakage current	I _{I-O}	Relative humidity = 45% Ta=25°C, t = 5 second V_{I-O} = 3000Vdc, (Note 10)	_	_	1	μА
Resistance (input-output)	R _{I-O}	V _{I-O} = 500V, R.H.≤ 60% (Note 10)	5×10 ¹⁰	10 ¹⁴	_	Ω
Capacitance (input-output)	C _{I-O}	f = 1MHz, (Note 10)	_	0.6	_	pF

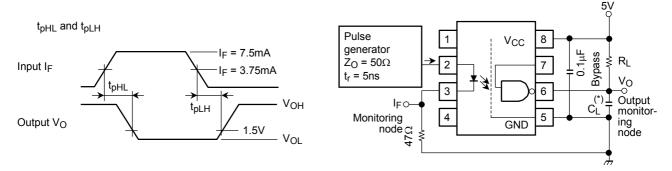
^(**)All typ.values are at V_{CC} = 5V, Ta = 25°C.

Switching Characteristics (Ta = 25°C, V_{CC} = 5 V)

Characteristic	Symbol	Test Circuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time to high output level	t _{pLH}		R _L = 350Ω, C _L = 15pF	_	60	75	ns
Propagation delay time to low output level	t _{pHL}	1	$I_F = 7.5 \text{mA}$ (Note 2), (Note 3),	ı	60	75	ns
Output rise time(10–90%)	t _r		(Note 4)&(Note 5)	_	30	_	ns
Output fall time(90–10%)	t _f			1	30	I	ns
Propagation delay time of enable from V _{EH} to V _{EL}	tELH		$R_L = 350\Omega$, $C_L = 15pF$ $I_F = 7.5mA$	ı	25	ı	ns
Propagation delay time of enable from V _{EL} to V _{EH}	t _{EHL}	2	V _{EH} = 3.0V V _{EL} = 0.5V (Note 6)&(Note 7)	1	25	1	ns
Common mode transient immunity at high output level	СМН		$V_{CM} = 400V$ $R_L = 350\Omega$ $V_{O(min.)} = 2V$ $I_F = 0mA$, (Note 9)	1000	10000	ı	V/µs
Common mode transient immunity at low output level	CML	3	V_{CM} = 400V R_L = 350 Ω $V_{O(max.)}$ = 0.8V I_F = 7.5mA, (Note 8)	-1000	-10000	ı	V/µs

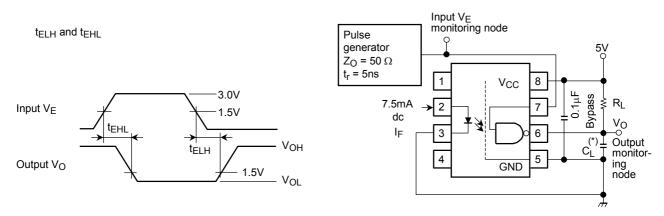
4 2002-09-25

Test Circuit 1.



(*) C_L is approximately 15pF which includes probe and stray wiring capacitance.

Test Circuit 2.

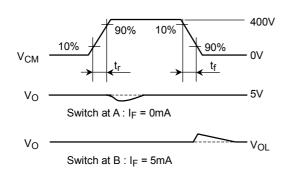


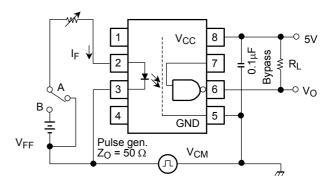
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(*) C_L is approximately 15pF which includes probe and stray wiring capacitance.

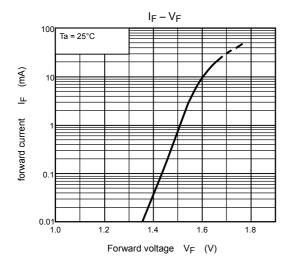
Test Circuit 3.

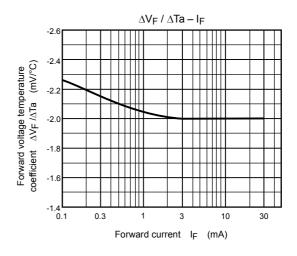
Transient Immunity and Typ. Waveforms.

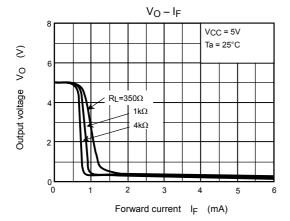


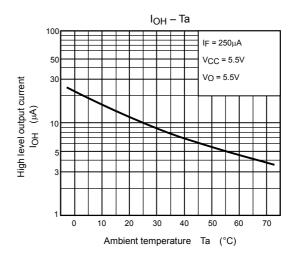


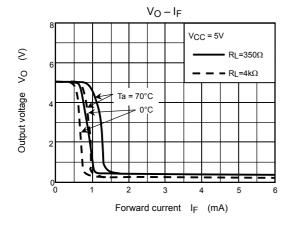
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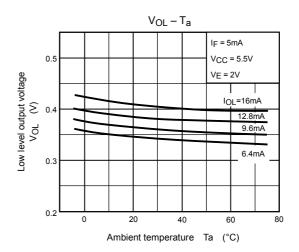


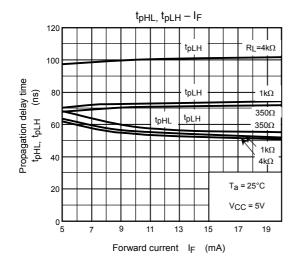


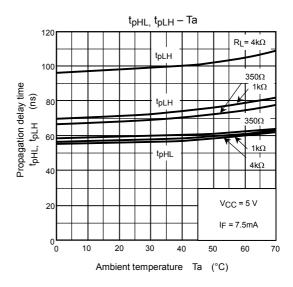


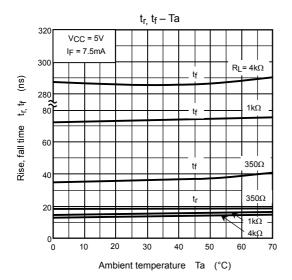


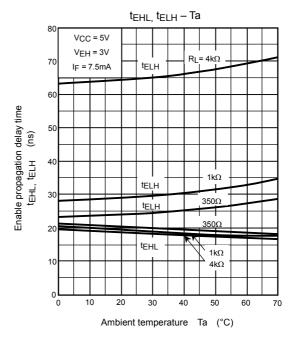












7

Notes

- 1. The V_{CC} supply voltage to each TLP2601 isolator must be bypassed by a $0.1\mu F$ capacitor of larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close aspossible to the package V_{CC} and GND pins of each device.
- 2. t_{pHL} Propagation delay is measured from the 3.75mA level on the low to high transition of the input current pulse to the 1.5V level on the high to low transition of the output voltage pulse.
- 3. tpLH Propagation delay is measured from the 3.75mA level on the high to low transition of the input current pulse to the 1.5V level on the low to high transition of the output voltage pulse.
- 4. tf Fall time is measured from the 10% to the 90% levels of the high to low transition on the output pulse.
- 5. t_r Rise time is measured from the 90% to 10% levels of the low to high transition on the output pulse.
- 6. tehl · Enable input propagation delay is measured from the 1.5V level on the low to high transition of the input voltage pulse to the 1.5V level on the high to low transition of the output voltage pulse.
- 7. telh Enable input propagation delay is measured from the 1.5V level on the high to low transition of the input voltage pulse to the 1.5V level on the low to high transition of the output voltage pulse.
- 8. CML The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state (i.e., $V_{OUT} < 0.8V$).

 Measured in volts per microsecond (V / μ s).
- 9. CMH The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the high state (i.e., $V_{OUT} > 2.0V$).

 Measured in volts per microsecond(V / μ s).

 Volts/microsecond can be translated to sinusoidal voltages:

$$V / \mu s = \frac{(\text{dv}_{CM})}{\text{dt}}_{\text{Max.}} = f_{CM} V_{CM} (p.p.)$$

Example:

 $V_{CM} = 318V_{pp}$ when $f_{CM} = 1MHz$ using CML and CMH = 1000V / μs data sheet specified minimum.

- 10. Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and Pins 5, 6, 7 and 8 shorted together.
- 11. Enable · No pull up resistor required as the device has an internal pull up resistor. input

8

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